

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions or listing of claims for this application:

Listing of Claims:

Claims 1-8 (Canceled).

9. (New) A semiconductor apparatus formed on a semiconductor substrate having a first conductivity type, comprising:

an internal circuit formed on the semiconductor substrate;

a plurality of external connection terminals formed in a first portion of said semiconductor substrate around said internal circuit, said external connection terminals being electrically connected to said internal circuit, wherein a plurality of power supply voltages are provided to said external connection terminals; and

one or more outer ESD elements formed in a second portion of said semiconductor substrate or in a common well region in said semiconductor substrate, around the first portion of said semiconductor substrate;

wherein said outer ESD element further comprises:

a first terminal electrically connected to a higher voltage level of a main power supply;

a second terminal electrically connected to a lower voltage level of the main power supply; and

a third terminal electrically connected to said external connection terminals.